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| 1. | Soft breakdown conduction in ultrathin (3-5 nm) gate dielectrics By: Miranda, E; Sune, J; Rodriguez, R; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 47 Issue: 1 Pages: 82-89 Published: JAN 2000 | 1 | 3 | 0 | 2 | 0 | 81 | 4.50 |
| 2. | Voltage and Power-Controlled Regimes in the Progressive Unipolar RESET Transition of HfO2-Based RRAM By: Long, Shibing; Perniola, Luca; Cagli, Carlo; et al. SCIENTIFIC REPORTS Volume: 3 Article Number: 2929 Published: OCT 14 2013 | 2 | 24 | 20 | 23 | 1 | 70 | 14.00 |
| 3. | Quantum-size effects in hafnium-oxide resistive switching By: Long, Shibing; Lian, Xiaojuan; Cagli, Carlo; et al. APPLIED PHYSICS LETTERS Volume: 102 Issue: 18 Article Number: 183505 Published: MAY 6 2013 | 8 | 25 | 17 | 20 | 0 | 70 | 14.00 |
| 4 . | Electron transport through broken down ultra-thin SiO2 layers in MOS devices By: Miranda, E; Sune, J MICROELECTRONICS RELIABILITY Volume: 44 Issue: 1 Pages: 1-23 Published: JAN 2004 | 7 | 6 | 2 | 5 | 0 | 70 | 5.00 |
| 5. | A function-fit model for the soft breakdown failure mode By: Miranda, E; Sune, J; Rodriguez, R; et al. IEEE ELECTRON DEVICE LETTERS Volume: 20 Issue: 6 Pages: 265-267 Published: JUN 1999 | 1 | 1 | 1 | 1 | 0 | 68 | 3.58 |
| 6. | A Model for the Set Statistics of RRAM Inspired in the Percolation Model of Oxide Breakdown By: Long, Shibing; Lian, Xiaojuan; Cagli, Carlo; et al. | 3 | 25 | 16 | 22 | 1 | 67 | 13.40 |

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| | IEEE ELECTRON DEVICE LETTERS Volume: 34 Issue: 8 Pages: 999-1001 Published: AUG 2013 | | | | | | | |
| 7. | Model for the Resistive Switching Effect in HfO2 MIM Structures Based on the Transmission Properties of Narrow Constrictions By: Miranda, Enrique A.; Walczyk, Christian; Wenger, Christian; et al. IEEE ELECTRON DEVICE LETTERS Volume: 31 Issue: 6 Pages: 609-611 Published: JUN 2010 | 17 | 12 | 16 | 10 | 1 | 67 | 8.38 |
| 8. | Impact of Temperature on the Resistive Switching Behavior of Embedded HfO2-Based RRAM Devices By: Walczyk, Christian; Walczyk, Damian; Schroeder, Thomas; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 58 Issue: 9 Pages: 3124-3131 Published: SEP 2011 | 7 | 11 | 19 | 14 | 0 | 61 | 8.71 |
| 9. | Resistive switching in hafnium dioxide layers: Local phenomenon at grain boundaries By: Lanza, M.; Bersuker, G.; Porti, M.; et al. APPLIED PHYSICS LETTERS Volume: 101 Issue: 19 Article Number: 193502 Published: NOV 5 2012 | 10 | 15 | 13 | 17 | 0 | 55 | 9.17 |
| 10. | Cycle-to-Cycle Intrinsic RESET Statistics in HfO2-Based Unipolar RRAM Devices By: Long, Shibing; Lian, Xiaojuan; Ye, Tianchun; et al. IEEE ELECTRON DEVICE LETTERS Volume: 34 Issue: 5 Pages: 623-625 Published: MAY 2013 | 1 | 20 | 16 | 16 | 0 | 53 | 10.60 |
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